

AMENDMENTS TO THE CLAIMS

Please amend the claims as indicated below. The language being added is underlined (“___”) and the language being deleted contains strikethrough (“—”):

1. – 5. (canceled)

6. (currently amended) A transistor circuit for implementing a differential switch, comprising:

a first switch node configured to connect to an external circuit;

a second switch node configured to connect to the external circuit;

a first transistor device having a first terminal connected to the first switch node, a second terminal, and a third terminal configured to receive a control signal that controls the electrical connectivity between the first terminal and the second terminal;

a second transistor device having a first terminal connected to the second terminal of the first transistor device, a second terminal connected to the second switch node, and a third terminal configured to receive the control signal; and

a third transistor device having a first terminal connected to the first terminal of the first transistor device, a second terminal connected to the second terminal of the second transistor device, and a third terminal configured to receive the control signal, the third transistor device configured with predetermined parasitic characteristics that improve the effective parasitic characteristics of the transistor circuit ~~effect of the parasitic characteristics of the transistor circuit when the control signal enables the first transistor device, the second transistor device, and the third transistor device.~~

7. (original) The transistor circuit of claim 6, wherein the first transistor device, the second transistor device, and the third transistor device are each a metal-oxide-semiconductor field-effect transistor.

8. - 9. (canceled)

10. (currently amended) The transistor circuit of claim 6, wherein the predetermined parasitic characteristics of the third transistor device reduce the ~~effective effect of the~~ parasitic resistance of the transistor circuit while sustaining a less than equivalent increase in ~~effective the effect of the~~ parasitic capacitance of the transistor circuit.

11. - 12 (canceled)